X-ray induced oxygen vacancies at the LaAlO$_3$/SrTiO$_3$ interface switch dimensionality of the mobile electron system

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Oxygen deficient LaAlO$_3$/SrTiO$_3$ (OD-LAO/STO) heterostructures are characterised by a dichotomic electron system, in which mobile delocalized Ti $t_{2g}$-electrons co-exist with Ti $e_g$-ones localized at oxygen vacancies ($V_O$s). Here, we explore OD-LAO/STO heterostructures, where the $V_O$s are generated by X-ray irradiation at $T = 12$K. We determine the fundamental $k$-resolved electronic structure characteristics of this system, including electron dispersions and Fermi surface of the mobile electron system, using resonant soft-X-ray ARPES. Despite the narrow interfacial localization, the X-ray generated $V_O$s switch the dimensionality of the interfacial electrons from 2D, characteristic of the standard stoichiometric LAO/STO interface, to quasi-3D extending into STO over a depth of more than 10 nm.
Introduction

Transition-metal oxides (TMOs) presently play one of the forefront roles in theoretical and experimental condensed matter research (for entries see Tokura & Nagaosa 2000). An involved interplay between the spin, charge, orbital and lattice degrees of freedom in these materials results in a wealth of phenomena interesting from the fundamental point of view and bearing potential for technological applications. These include rich electronic and magnetic phase diagram, metal-insulator transitions, colossal magnetoresistance, ferroelectricity, multiferroicity, high-\(T_c\) superconductivity, etc. Interfaces and heterostructures of TMOs can add another dimension to their fascinating properties, giving rise to physical phenomena which cannot be anticipated from the properties of individual constituents, with the new functionalities having great promise for future device applications (see, for example, the review Mannhart & Schlom 2010).

The interface between LaAlO\(_3\) (LAO) and SrTiO\(_3\) (STO) is a paradigm example of new functionalities formed at TMO interfaces. Although these materials in their bulk form are band insulators, their interface spontaneously forms a mobile electron system (MES) (see, for example, Mannhart & Schlom 2010; Hwang 2012). Its high electron mobility co-exists with superconductivity, ferromagnetism, large magnetoresistance and other non-trivial phenomena which can in addition be tuned with field effect. The MES electrons are localized at the STO side of the interface and populate the Ti \(t_{2g}\)-derived in-plane \(d_{yz}\), states and out-of-plane \(d_{ax^2-y^2}\) states (Delugas 2011, King 2014, Cancellieri 2014). Two phenomena of crucial importance for virtually all physical properties of LAO/STO are (1) polaronic nature of the charge carriers, where strong electron-phonon coupling to the LO3 phonon mode reduces their low-temperature mobility by a factor of about 2.5, and coupling to the soft TO1 polar mode dramatically reduces mobility with temperature (Cancellieri 2016, Strocov 2018), and (2) electronic phase separation (EPS) where the conducting MES puddles are embedded in the insulating host phase (Scopigno 2016, Strocov 2018).

Oxygen vacancies \(\left[V_{o}\right]_s\) in oxides and at their interfaces dramatically affect their electronic and magnetic properties. In a simplified picture, each (neutral) \(V_{o}\) in the perovskite ABO\(_3\)-structure releases two electrons from the B-cation. For the LAO/STO interface, the \(V_{o}\) on the LAO side may not only form localized states within the LAO layer, but transfer to lower-lying empty states on the STO side of the interface and contribute to the MES (see, for example, Bristowe 2011; Li 2011; Yu & Zunger 2014). For the \(V_{o}\) on the STO side of the interface (if not stated otherwise, hereinafter the tag \(V_{o}\) will imply those in STO) one of the two electrons released by Ti atoms at each \(V_{o}\) joins the MES formed by delocalized quasiparticles, which are Ti \(t_{2g}\)-derived, weakly correlated, non-magnetic and form large polarons (Cancellieri 2016). The injected MES electrons affect the polaronic coupling and thus mobility of the interfacial charge carriers (Wang 2016, Cancellieri 2016). Furthermore, sufficiently high concentrations of \(V_{o}\) result in a dimensionality transformation of the MES from 2D to quasi-3D (Herranz 2007; Basletic 2008; Li 2011). The other of the two electrons released at each \(V_{o}\) stays near the Ti ion to form there localized in-gap states (IGSs) at binding energy \(E_b \sim -1.3\) eV, which are Ti \(e_g\)-derived, strongly correlated, magnetic and are often viewed as small polarons. The IGS-subsystem determines the interfacial ferromagnetism of OD-LAO/STO, where crucial are various atomic configurations of the \(V_{o}\) (Lechermann 2014; Behrmann and Lechermann 2015). This picture of the dichotomic electron system at the OD-LAO/STO interface (see, for example, Luo 2004; Pavlenko 2012; Pavlenko 2013; Lin & Demkov 2013; Janotti 2014; Lechermann 2014; Lechermann 2016; Altmeyer 2016; Sing 2017) has recently been experimentally confirmed by resonant photoemission (ResPE) results of Chikina (2018). We note however that the electron distribution between the MES and IGSs may depend on particular configurations of \(V_{o}\)-s; for example, LDA+U calculations on bare STO surfaces (Jeschke 2015) suggest that while for \(V_{o}\)-s in cluster configurations the electrons distribute between the MES and IGSs evenly, isolated \(V_{o}\)-s on the surface tend to donate both released electrons into the MES. The coexistence of the two radically different MES and IGS electron subsystems enriches hugely the physics of the
OD-LAO/STO interfaces compared to the stoichiometric ones. We note in passing that the $V_\text{O}$s can also tune the nanoscale structure of the MES within the EPS picture (Strocov 2019).

Here, we explore OD-LAO/STO heterostructures where the $V_\text{O}$s are generated by X-ray irradiation. We investigate the processes of their formation and migration by Secondary Ion Mass Spectrometry (SIMS) depth profiling of samples, irradiated in $^{18}$O atmosphere to fill these $V_\text{O}$s by the $^{16}$O isotope. Furthermore, we determine the electronic structure of these OD-LAO/STO heterostructures using resonant soft-X-ray ARPES. Despite the narrow interfacial localization, the X-ray generated $V_\text{O}$s switch the dimensionality of the interfacial MES from 2D, characteristic of the stoichiometric LAO/STO, to quasi-3D extending deep into STO.

**Sample preparation**

The LAO/STO samples with a LAO layer thickness of 4 u.c. on top of TiO$_2$-terminated STO(100) were grown with Pulsed Laser Deposition. We followed a non-standard growth protocol, where the STO substrate was annealed at 500°C in vacuum, the O$_2$ pressure during the LAO deposition at 720°C reduced to 8×10$^{-5}$ mbar, and the post-growth annealing performed ex-situ (Chikina 2018, Strocov 2019). Although these samples were finally stoichiometric, they readily built up $V_\text{O}$s under X-ray irradiation. This was evidenced by the spectroscopic signatures of $V_\text{O}$s, the IGS peak in the VB and Ti$^{3+}$ component of the Ti 2p core level spectra, which had vanishing weight in the beginning of X-ray irradiation and then gradually scaled up. The creation of the $V_\text{O}$s can be explained by that X-rays modify the chemical potential of oxygen in the solid (Yang 2018, Fleig 2019). This provides the driving force for oxygen to leave the solid, leaving behind the $V_\text{O}$. This process can be reversed by exposure of the LAO/STO samples to X-ray irradiation in O$_2$ pressure of about 10$^{-7}$ mbar that quenches the X-ray generated $V_\text{O}$s. The high efficiency of this reaction can be explained by that X-ray irradiation cracks the physisorbed O$_2$ molecules into atomic oxygen (Dudy 2016; Gabel 2017) which can effectively penetrate into the LAO/STO heterostructure.

**Electronic structure overview**

Our SX-ARPES experiments used ResPE at the Ti L-edge boosting response of the Ti derived electron states at the buried LAO/STO interface. The measurements were performed at the SX-ARPES endstation (Strocov 2014-1) of the Advanced Resonant Spectroscopies (ADRESS) beamline (Strocov 2010) of the Swiss Light Source, Paul Scherrer Institute, Switzerland. The photon flux was around 10$^{13}$ photons/sec and focused into a spot size of 30 x 75 μm$^2$ in projection on the sample surface at an X-ray grazing incidence angle of 15°. The XAS data were measured in the total electron yield (TEY) mode. For the ARPES measurements, the combined (beamline and analyzer) energy resolution was set to ~50 meV. The sample temperature was kept at 12 K in order to suppress smearing of the coherent spectral structure (Braun 2013) as well as allow a build-up of the $V_\text{O}$s.

Our ResPE experiment not only boosts the weak response of the interfacial electrons (Drera 2011, Koitzsch 2011, Berner 2013, Cancellieri 2013, Drera 2014), further reduced by the EPS (Strocov 2019), but also allows elemental and chemical state analysis of the electron states (Olson 1996; Molodtsov 1997). Fig. 1 (a) shows the XAS spectrum through the Ti $L_1$ and $L_2$-edges (2p$_{1/2}$ and 2p$_{3/2}$ core levels, respectively) acquired at $t_{\text{IRR}}$ of about 2 hrs. The pairs of salient XAS peaks at each edge are formed by the Ti$^{4+}$ $e_g$ and $t_{2g}$ states. The corresponding map of ResPE intensity as a function of $E_g$ and excitation energy $hv$ is displayed in Fig. 1 (b). Above the broad valence band (VB) composed of the O 2p states in STO and LAO, the map shows the resonating broad IGS peak at $E_g \sim -1.3$ eV which is a hallmark of the $V_\text{O}s$. Recent analysis of its resonant behavior (Chikina 2018) confirms that the IGS-subsystem is derived from $e_g$ states of the Ti$^{3+}$ ions pushed down in energy by strong electron correlations (Pavlenko 2012; Pavlenko 2013; Lechermann 2014; Lechermann 2016). The narrow resonating peak at the Fermi energy ($E_F$) identifies the $t_{2g}$-derived MES. Its resonant excitation energy is delayed from the Ti$^{4+}$ $t_{2g}$ to Ti$^{4+}$ $e_g$ peak in the XAS spectrum due to remnant
k-conservation between the intermediate- and final-state wavefunctions coupled in the ResPE process (Chikina 2018).

Fig. 1. ResPE of OD-LAO/STO: (a) XAS spectrum and (b) angle-integrated ResPE intensity through the \( L_2 \) and \( L_3 \) edges. The resonating peak at \( E_g \) signals the \( t_{2g} \)-derived MES and the one at \( E_g \sim 1.3 \text{ eV} \) the IGS characteristic of the \( V_oS \); (c) ARPES image, enhancing the \( d_{vy} \)-band, measured at the \( hv \)-value and in the \( E_g \)-interval marked at (b).

We note that Ti\( ^{3+} \) \( e_g \) and \( t_{2g} \) signals in the XAS spectrum in Fig. 1 (a), corresponding to the Ti atoms hosting the \( V_oS \), are almost invisible. At the same time, the IGS signal in the ResPE map (b), corresponding to the Ti\( ^{3+} \) \( e_g \) states of these atoms, is profound. This observation is consistent with the localization of the \( V_oS \) within the top STO layer, because the width of this region is much smaller than the probing depth of the TEY-XAS measurements of the order of 5 nm, and comparable with that of SX-ARPES measurements of the order of 1.1 nm at our excitation energy (Gabel 2017).

The image (c) in Fig. 1 shows the ARPES intensity measured at \( hv = 466.4 \text{ eV} \), enhancing the \( d_{vy} \)-band in comparison to the \( d_{vy} \)-one (Chikina 2018), superimposed with a sketch of the \( t_{2g} \)-dispersions. We note that the band order and band dispersions observed for OD-LAO/STO show the same pattern as for ST-LAO/STO. However, the observed band filling is somewhat larger, as characterized by the Fermi momentum \( k_F \) of the \( d_{vy} \) band in Fig. 1 increased to \( \sim 0.4 \text{ Å}^{-1} \) compared to \( \sim 0.33 \text{ Å}^{-1} \) for ST-LAO/STO (Cancellieri 2014; 2016). The downward shift of this band hints on a slower electrostatic potential increase into the STO bulk compared to ST-LAO/STO. Furthermore, the weight of the polaronic hump and thus renormalization of the effective mass \( m^* \) reduce to \( \sim 1.5 \) compared to \( \sim 2.5 \) in ST-LAO/STO (Cancellieri 2016). Importantly, as we will see below, the oxygen deficiency changes the dimensionality of the MES.

**Dimensionality of the MES**

In order to confirm the dimensionality of the MES in OD-LAO/STO, we investigated its ARPES response as a function of out-of-plane momentum \( k_z \) varied in an extended \( hv \)-range above the Ti \( L \)-edge. The measurements were performed under a saturation dose of X-ray irradiation of about 2 hrs. Because of the much weaker off-resonance response of the MES, such measurements are extremely photon hungry. We used \( p \)-polarization of incident X-rays to switch from the two-band combination of the \( d_{vy} \) and \( d_{vy} \) antisymmetric states to the single-band \( d_{vy} \) state. The X-ray grazing incidence angle for these measurements was increased by \( 8^\circ \) compared to the above standard setting in order to enhance the \( d_{vy} \)-intensity in the
second Brillouin zone (BZ). Fig. 2 shows an experimental map of ARPES intensity at $E_{\mathrm{F}}$ as a function of $h\nu$, rendered into the out-of-plane momentum $k_z$ according to the relation $k_z = \sqrt{\frac{2m(E_{\mathrm{F}}+V_0)}{\hbar^2} - \frac{k^2_{||}}{\hbar^2}}$, where $m$ is the free-electron mass, $E_{\mathrm{F}}$ photoelectron kinetic energy, $V_0$ the inner potential set to 10 eV, and $p_z$ the photon momentum correction in our experimental geometry (Strokov 2014-1). The map clearly shows FS contours of the $d_{xz}$-derived interfacial states whose intensity periodically blows up near the $\Gamma$-points in $k_z$. This pattern alone does not indicate the 3D character of these states, because even if the out-of-plane $d_{xz}$-orbitals formed 2D states confined in the interfacial QW, they would also produce periodic intensity oscillations. In this case, however, the absence of their out-of-plane dispersion would show up as straight FS contours in the $(k_x,k_y)$ coordinates (for in-depth analysis of photoemission response of 2D states see Strokov 2018). In our case the FS contours, although distorted by variations of the photoemission imatrix element, are rounded in the $(k_x,k_y)$-coordinates indicating $k_z$-dispersion and thus quasi-3D character of the interfacial states in OD-LAO/STO. Although the acquisition of this dataset has required $\sim$3 hrs, more accurate analysis of these off-resonance data will require much better experimental statistics.

Fig. 2. The $d_{xz}$-contours of the FS as a function of $k_z$ in an extended $h\nu$-range. The corresponding $h\nu$-values are marked. The rounded FS contours indicate the quasi-3D character of the out-of-plane MES states.

Do the MES electrons, developing under irradiation, stay confined at the interface and keep their 2D character or expand into the STO bulk and become quasi-3D? To answer this question, we investigated the out-of-plane dispersion of the OD-LAO/STO states at their saturation after X-ray irradiation for about 2 hours. At fixed resonant $h\nu = 466.4$ eV delivering maximal intensity to the $d_{xz}$-states, the out-of-plane momentum $k_z$ was varied via $k_{||}$ (see the above relation).
The measured ARPES image through two BZs is presented in Fig 4 (b) together with the gradient \( \frac{dI}{d|k|} \) of the momentum-distribution curve (MDC) \( I \) at \( E_F \) (Fermi intensity) whose extremes identify the Fermi momentum \( (k_F) \) values. We see that the apparent \( k_F \) of the \( d_{xz} \)-bands reduces from 0.40 Å\(^{-1} \) in the first BZ to 0.29 Å\(^{-1} \) in the second one. As sketched in Fig. 3 (c), this peculiarity pins down their 3D character where the \( k_F \)-coordinate of \( k_F \) depends on \( k_F \) varying through the BZs. We note that, accidentally, our \( h\nu \) values near the Ti L-edge bring \( k_F \) to the \( \Gamma \)-point of the Brillouin zone (BZ) of bulk STO. Remarkably, for the ST-samples the ARPES variations with \( k_F \) are qualitatively different: the \( d_{xz} \)-bands vary through the BZs only in the intensity of their ARPES response, but their \( k_F \) ~ 0.33 Å\(^{-1} \) stays constant (Cancellieri 2014) identifying the 2D character of MES in these samples. This fact is confirmed by another ARPES dataset, used for identification of polaronic nature of the LAO/STO charge carriers (Cancellieri 2016), which has been analyzed in the same way as the OD-LAO/STO data in Fig. 3 (see Supplementary Materials 1).

Discussion

The extended quasi-3D character of the MES in our samples, identified in the ARPES experiment, might seem puzzling in view of the 2D character of the \( V_{O} \)-system located within the top STO layer, suggested by the SIMS results. However, this peculiarity finds its explanation on the theoretical side, for example, in supercell DFT calculations by Li (2011) performed for different concentrations and spatial location of the \( V_{O} \). These calculations suggest that whereas the \( V_{O} \) in LAO contribute to the MES essentially 2D electrons localized within few atomic layers at the interface, each of the \( V_{O} \) in STO bulk creates around it an extended cloud of \( t_{2g} \)-derived states with a radius of the order of 150 Å. Even if the \( V_{O} \) are confined in the top layer of STO without diffusion into the bulk, which is our case of the X-ray generated \( V_{O} \), such delocalization of the electron wavefunctions deep into the STO bulk is sufficient to form a quasi-3D electron system observed in our ARPES experiment. We note however that the latter does not resolve any clear signature of the predicted 2D electrons localized at the interface, likely owing to their small overlap with the extended photoemission final states in our high-energy ARPES experiment. In any case, the problem of the multicomponent MES created in interplay of the \( V_{O} \) on both LAO and STO side with the interfacial electrostatic field requires further theoretical research. Our results are consistent with those of Plumb et al (2014) obtained for X-ray irradiated STO, where the emergent MES can be related exclusively to the \( V_{O} \) without any intrinsic polar discontinuity contribution (Gabel 2016, Dudy 2017). Similarly to the OD-LAO/STO, this system also shows quasi-3D character of the MES. We note that the above picture of the
localized 2D-layer of $V_0$'s forming the extended quasi-3D MES is actually similar to the conventional semiconductors, where tiny dopant concentrations on the promille level can form delocalized electron gas.

Which concentration of $V_0$'s switches the dimensionality of the MES? The previous work on LAO/STO samples prepared under the same growth and X-ray irradiation protocols (Strocov 2019) has shown that the MES puddles, formed at the interface by the EPS, maintain virtually constant k-space parameters of the band structure and Fermi surface in a wide range of $V_0$-concentration starting from less than 1% and towards its saturation value in this work. Therefore, the MES acquires its quasi-3D character already at the percent level of $V_0$'s in the top STO layer. This surprising fact can be understood based on the calculations by Li (2011) discussed above, which predict a spatial extension of the MES wavefunctions of the order of 150 Å [21]. This extension significantly exceeds the spatial separation of the $V_0$'s, which is only ~40 Å for the $V_0$-concentration of 1%, allowing effective overlap of the corresponding MES wavefunctions. Therefore, the MES at the OD-LAO/STO interface appears in its virtually saturated state (apart from its nanoscale structure described by the EPS picture) starting already from minute $V_0$-concentrations.

OD-LAO/STO interfaces have previously been studied by a number of techniques other than ARPES. It has been noted that their $n_s$ can be two-three orders of magnitude larger than $n_s = 0.5$ e per unit-cell area predicted by the polarity arguments. This fact alone necessitates the existence of an extended and thus quasi-3D component of the MES in OD-samples. This component has been identified, for example, by magnetotransport (Herranz 2007) and conducting-tip atomic force microscopy of the interfacial cross-section (Basletic 2008). Electron mobility in it could significantly exceed that of the paradigm 2DES in ST-LAO/STO (Herranz 2007, Kalabukhov et al, Cancellieri 2010); this phenomenon could trace back to stronger electron screening of the polaronic effects and thus smaller $m^*$-renormalization in OD-LAO/STO (Cancellieri 2016). However, the $V_0$ distribution profile in these OD-samples could extend into STO by a few thousands Å and more, with the diffusion processes being much affected by domain walls (see, for example, Kaliski 2013; Kim 2015; Yazdi-Rizi 2017). In our experiment, in contrast, the distribution profile of the X-ray generated $V_0$'s is confined at most within the top STO layer.

The effect of the X-ray generated $V_0$'s on the mobility of the interfacial charge carriers should critically depend on their orbital character. The defect scattering, associated with these $V_0$'s localized in the top STO layer, will affect mostly the $d_{xy}$-states localized in the narrow interfacial region, and much less the $d_{x^2-y^2}$-states extending farther into the STO bulk. Furthermore, the $V_0$'s increase this extension and thus suppress the sensitivity of the $d_{x^2-y^2}$-states to all other defects, whose concentration maximizes at the LAO/STO border as demonstrated, for example, by lineshape analysis of the SX-ARPES spectra by Cancellieri et al (2016). This effect bears a similarity to the concept of the semiconductor high-electron-mobility semiconductor transistors (HEMT) where the wavefunction localization away from the defect-rich region dramatically reduces defect scattering (Lev 2018, Schutz 2017). For both $d_{xy}$- and $d_{x^2-y^2}$-states, however, the mobile electrons injected by the $V_0$'s increase electron screening and thereby reduce the polaronic $m^*$-renormalization (Cancellieri 2016).

**Summary**

$V_0$'s at LAO/STO interfaces form a dichotomic electron system, where weakly correlated and non-magnetic delocalized MES-electrons coexist with strongly correlated and magnetic localized IGS-electrons. We have explored the oxygen deficiency profile and electronic structure of the OD-LAO/STO interfaces, where the $V_0$'s were created by X-ray irradiation at low sample temperature of 12K. Analysis of out-of-plane electron dispersions, measured by non-resonant and Ti 2p resonant ARPES, evidences that, although the X-ray generated $V_0$'s localize in the top STO layer, the resulting MES has a quasi-3D character consistent with its theoretically predicted depth extension of more than 10 nm. This finding demonstrates that the X-ray generated $V_0$'s cause the 2D to 3D dimensionality crossover of the MES already at minute $V_0$-concentrations.
of the order of 1% of the Ti atoms in the top STO layer. This finding opens the possibility of X-ray writing regions with variable MES dimensionality in oxide heterostructures.

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References


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Supplementary Information

2D character of MES at stoichiometric LAO/STO

In order to confirm the MES-dimensionality in the ST-LAO/STO samples by an independent dataset, we have revised the SX-ARPES data used for identification of polaronic nature of the LAO/STO charge carriers (Cancellieri 2016). The ARPES image from this dataset, presented in Fig. S1 (a), was acquired with s-polarized incident X-rays at the Ti $L_2$-edge to enhance the $d_{x^2-y^2}$-signal. The corresponding $E_F$-MDC gradient plot (b) shows the same $k_F \sim 0.33$ Å through the two BZs, identifying the purely 2D character of the MES.

**Fig. S1.** (a) Experimental ARPES image through two BZs; (b) $E_F$-MDC gradient, whose minima identify the $k_F$ values. The same $k_F$ values between the two BZs identify purely 2D character of the MES in ST-LAO/STO.